

## Super-Junction Power Mosfet

### 1. Product Information

#### Features

- Low FOM  $R_{DS(ON)} \times Q_G$
- Extremely Low Switching Loss
- Good Stability and Uniformity
- 100% UIS and Isolation Tested

#### Applications

- EV Charger
- Sever/Telecom/PC Power
- AC-DC Power Management
- Motor Driver

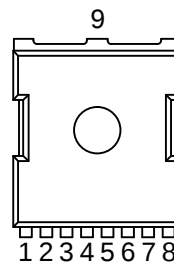
#### Quick reference

- $V_{DS} \geq 600\text{ V}$
- $I_D \leq 55\text{ A}$
- $R_{DS(ON)} \leq 68\text{ m}\Omega$  @  $V_{GS} = 10\text{ V}$  (Type 57 m $\Omega$ )

#### Pin Description

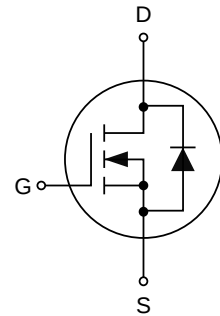
| Pin           | Description |
|---------------|-------------|
| 1             | Gate(G)     |
| 2,3,4,5,6,7,8 | Source(S)   |
| 9             | Drain(D)    |

#### Simplified Outline



Top View  
TOLL-8L

#### Symbol



#### Package Marking and Ordering Information

| Product Name | Marking    | Package | Packaging   | Quantity (pcs) |
|--------------|------------|---------|-------------|----------------|
| KJC60R068T   | KJC60R068T | TOLL-8L | Reel & Tape | 2000           |

### 2. Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise noted)

| Symbol                            | Parameter                                                       | Values     | Unit |
|-----------------------------------|-----------------------------------------------------------------|------------|------|
| $V_{DS}$                          | Drain-Source Voltage                                            | 600        | V    |
| $V_{GS}$                          | Gate-Source Voltage                                             | $\pm 30$   | V    |
| $I_D$                             | Continuous Drain Current (T <sub>C</sub> =25°C) <sup>[1]</sup>  | 55         | A    |
|                                   | Continuous Drain Current (T <sub>C</sub> =100°C) <sup>[1]</sup> | 38         | A    |
| $I_{DM}$                          | Pulsed Drain Current <sup>[1]</sup>                             | 220        | A    |
| $E_{AS}$                          | Single Pulsed Avalanche Energy <sup>[2]</sup>                   | 410        | mJ   |
| dv/dt                             | Peak Diode Recovery dv/dt                                       | 50         | V/ns |
| $P_D$                             | Power Dissipation                                               | 375        | W    |
| T <sub>J</sub> , T <sub>stg</sub> | Operating Junction and Storage Temperature Range                | -55 to 150 | °C   |
| $R_{\theta JA}$                   | Thermal Resistance, Junction-Ambient                            | 80         | °C/W |
| $R_{\theta JC}$                   | Thermal Resistance, Junction-Case                               | 2.3        | °C/W |

## 3. Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

| Symbol                             | Parameter                                 | Test Conditions                                                                          | Min | Type | Max  | Unit |
|------------------------------------|-------------------------------------------|------------------------------------------------------------------------------------------|-----|------|------|------|
| Static Characteristics             |                                           |                                                                                          |     |      |      |      |
| BV <sub>DSS</sub>                  | Drain-Source Breakdown Voltage            | V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA                                             | 600 | -    | -    | V    |
| I <sub>DSS</sub>                   | Zero Gate Voltage Drain Current           | V <sub>DS</sub> =600 V, V <sub>GS</sub> =0 V                                             | -   | -    | 10   | μA   |
| I <sub>GSS</sub>                   | Gate-Body Leakage Current                 | V <sub>GS</sub> =±30 V, V <sub>DS</sub> =0 V                                             | -   | -    | ±100 | nA   |
| V <sub>GS(th)</sub>                | Gate Threshold Voltage                    | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA                                | 3.0 | -    | 5.0  | V    |
| R <sub>DS(ON)</sub>                | Drain-Source On-State Resistance          | V <sub>GS</sub> =10 V, I <sub>D</sub> =27 A                                              | -   | 57   | 68   | mΩ   |
| Dynamic Characteristics            |                                           |                                                                                          |     |      |      |      |
| C <sub>iss</sub>                   | Input Capacitance                         | V <sub>DS</sub> =100 V, V <sub>GS</sub> =0 V, F=1 MHz                                    | -   | 3012 | -    | pF   |
| C <sub>oss</sub>                   | Output Capacitance                        |                                                                                          | -   | 145  | -    | pF   |
| C <sub>rss</sub>                   | Reverse Transfer Capacitance              |                                                                                          | -   | 2.9  | -    | pF   |
| Switching Characteristics          |                                           |                                                                                          |     |      |      |      |
| t <sub>d(on)</sub>                 | Turn-on Delay Time                        | V <sub>DS</sub> =400 V, I <sub>D</sub> =27 A, R <sub>G</sub> =25 Ω, V <sub>GS</sub> =10V | -   | 88   | -    | ns   |
| t <sub>r</sub>                     | Turn-on Rise Time                         |                                                                                          | -   | 75   | -    | ns   |
| t <sub>d(off)</sub>                | Turn-off Delay Time                       |                                                                                          | -   | 170  | -    | ns   |
| t <sub>f</sub>                     | Turn-off Fall Time                        |                                                                                          | -   | 50   | -    | ns   |
| Q <sub>g</sub>                     | Total Gate Charge                         | V <sub>DS</sub> =480 V, I <sub>D</sub> =27 A, V <sub>GS</sub> =10 V                      | -   | 79   | -    | nC   |
| Q <sub>gs</sub>                    | Gate-Source Charge                        |                                                                                          | -   | 21   | -    | nC   |
| Q <sub>gd</sub>                    | Gate-Drain Charge                         |                                                                                          | -   | 23   | -    | nC   |
| Source-Drain Diode Characteristics |                                           |                                                                                          |     |      |      |      |
| V <sub>SD</sub>                    | Drain-Source Diode Forward Voltage        | V <sub>GS</sub> =0V, I <sub>F</sub> =27 A                                                | -   | -    | 1.4  | V    |
| I <sub>S</sub>                     | Diode Continuous Forward Current          |                                                                                          | -   | -    | 55   | A    |
| I <sub>SM</sub>                    | Maximum Pulsed Body-Diode Forward Current |                                                                                          | -   | -    | 220  | A    |
| T <sub>rr r</sub>                  | Reverse Recovery Time                     | V <sub>R</sub> =400 V, I <sub>F</sub> =27 A, di/dt=100 A/μs                              | -   | 176  | -    | ns   |
| Q <sub>r</sub>                     | Reverse Recovery Charge                   |                                                                                          | -   | 1.4  | -    | μC   |

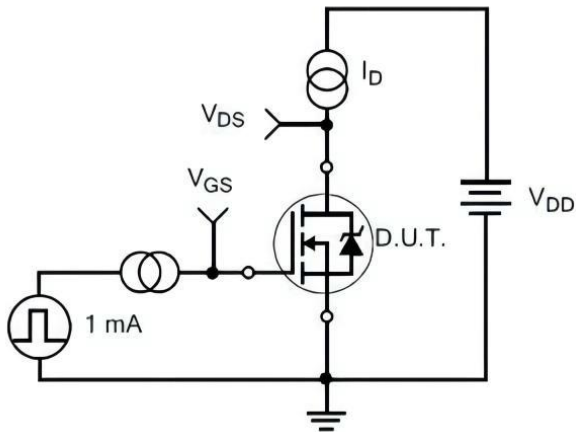
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. T<sub>J</sub>=25°C, V<sub>DD</sub>=50 V, V<sub>G</sub>=10 V, R<sub>G</sub>=25 Ω.

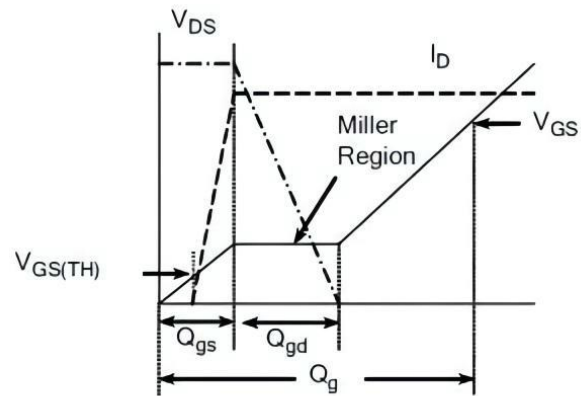
## 4. Test Circuits and Waveforms ( $T_J=25^{\circ}\text{C}$ )

**Table 1. Gate Charge Test Circuit and Waveforms**

**Gate Charge Test Circuit**

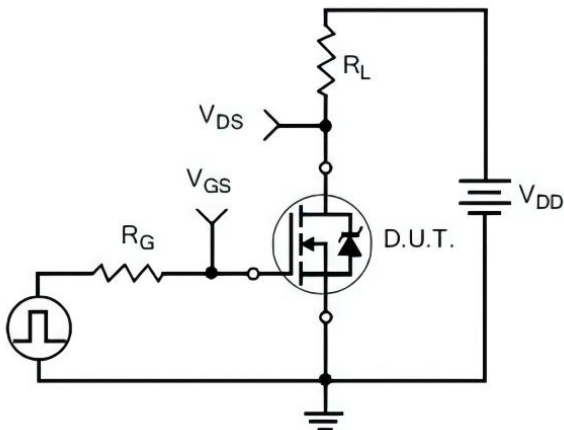


**Gate Charge Waveforms**

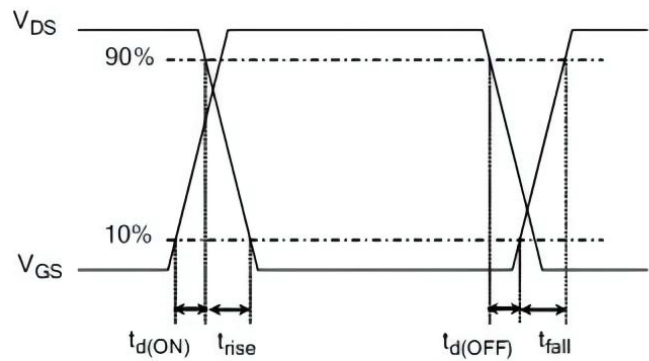


**Table 2. Resistive Switching Test Circuit and Waveforms**

**Resistive Switching Test Circuit**

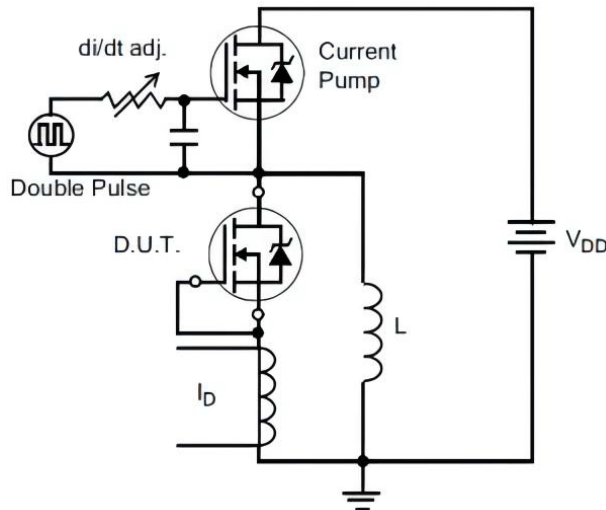


**Resistive Switching Waveforms**

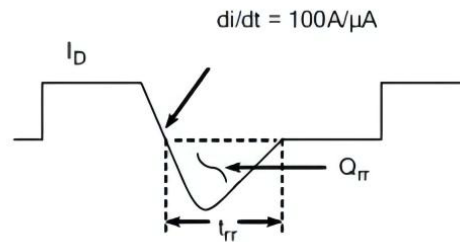


### Table 3. Diode Recovery Test Circuit and Waveforms

## Diode Recovery Test Circuit

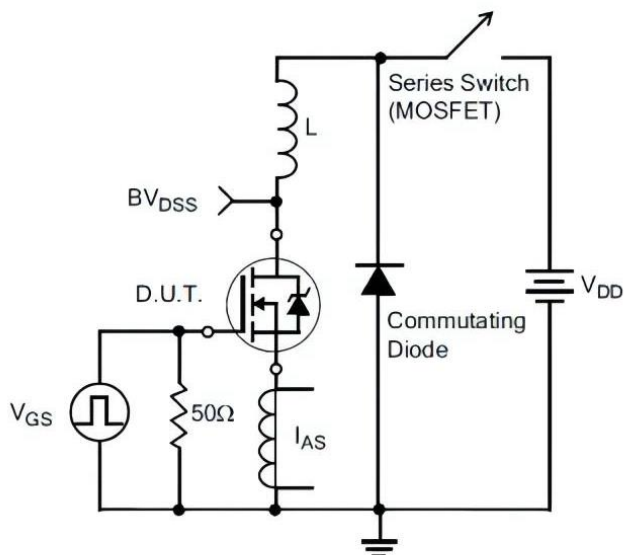


## Diode Recovery Waveforms

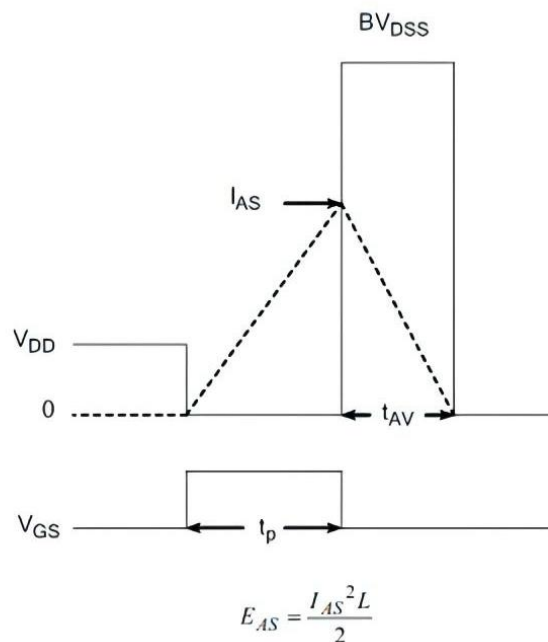


### Table 4. Unclamped inductive Switching (UIS) Test Circuit and Waveforms

### Unclamped Inductive Switching Test Circuit



## Unclamped Inductive Switching Waveforms



## 5. Electrical Characteristics

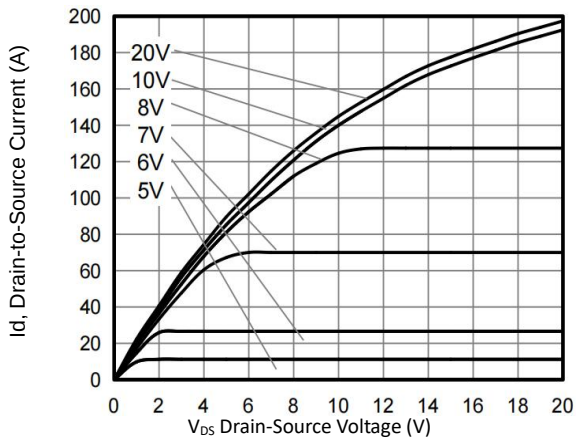


Figure 1. Typical Output Characteristics

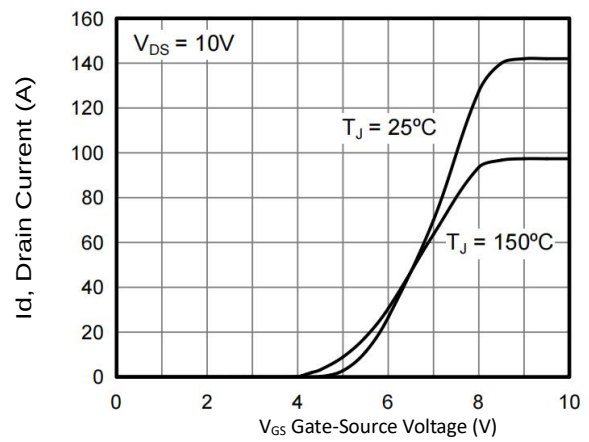


Figure 2. Typical Transfer Characteristics

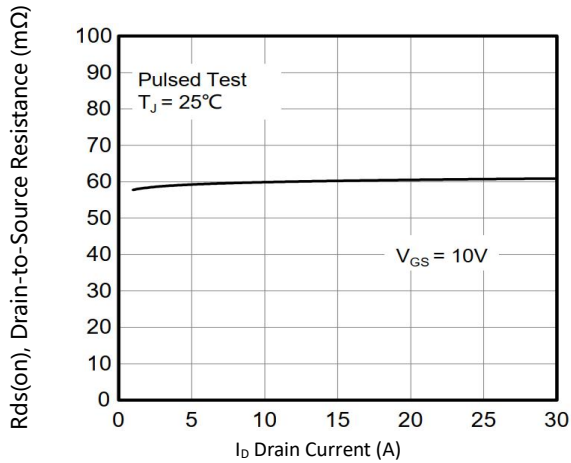


Figure 3. On-Resistance versus Drain Current

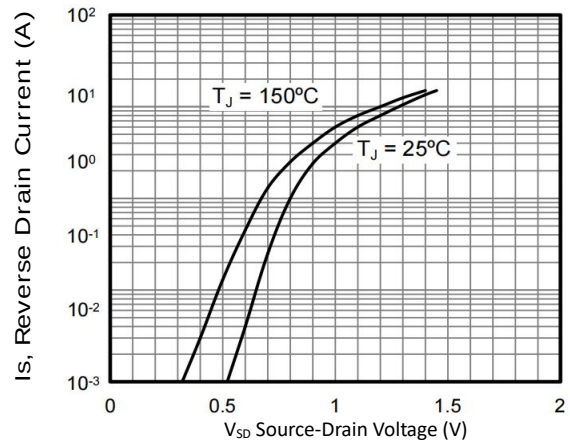


Figure 4. Diode forward voltage versus Current

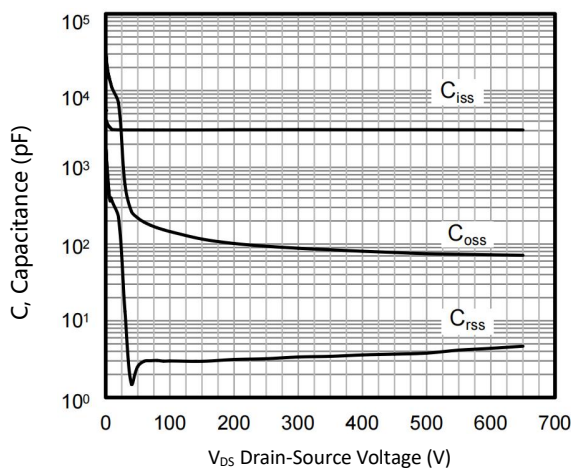


Figure 5. Typical Capacitance versus  $V_{DS}$

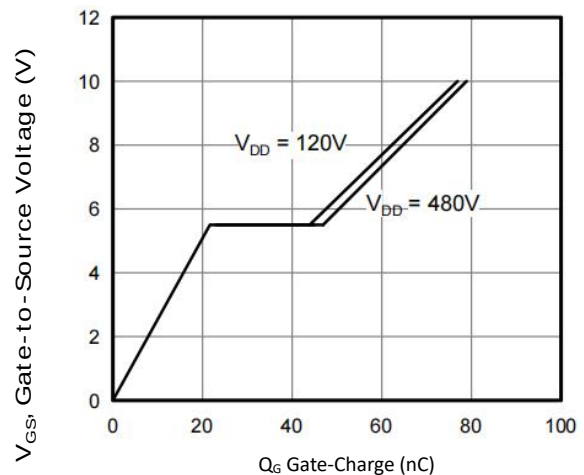


Figure 6. Typical Gate Charge versus  $V_{GS}$

## 5. Electrical Characteristics (cont.)

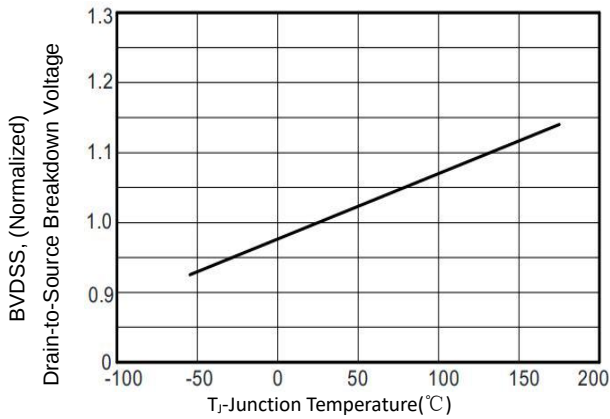


Figure 7.  $BV_{DSS}$  Variation with Temperature

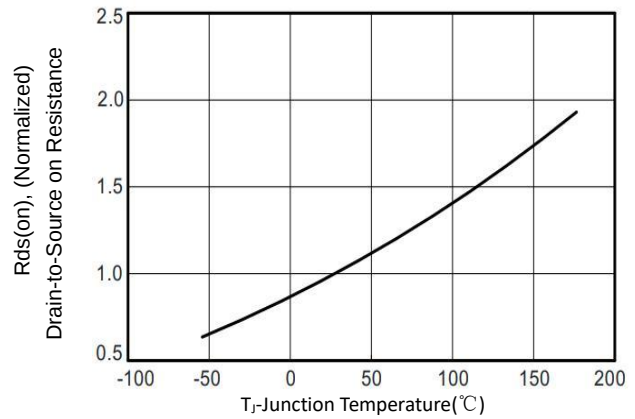


Figure 8. On-Resistance Variation with Temperature

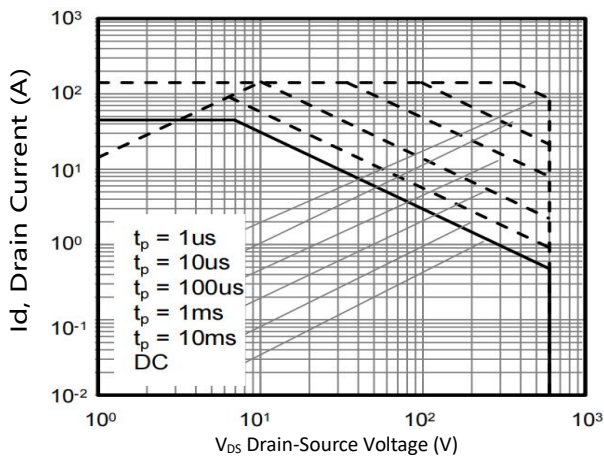


Figure 9. Maximum Safe Operating Area

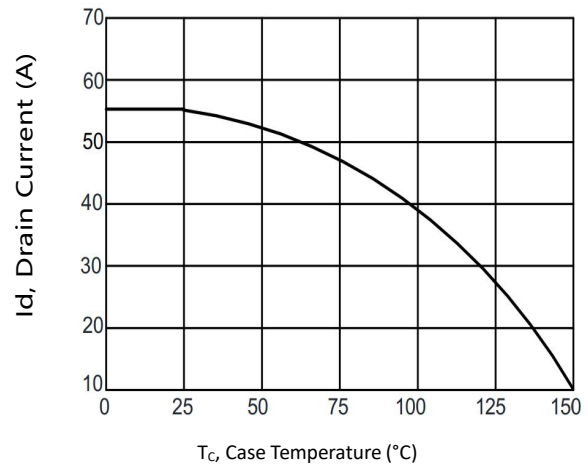
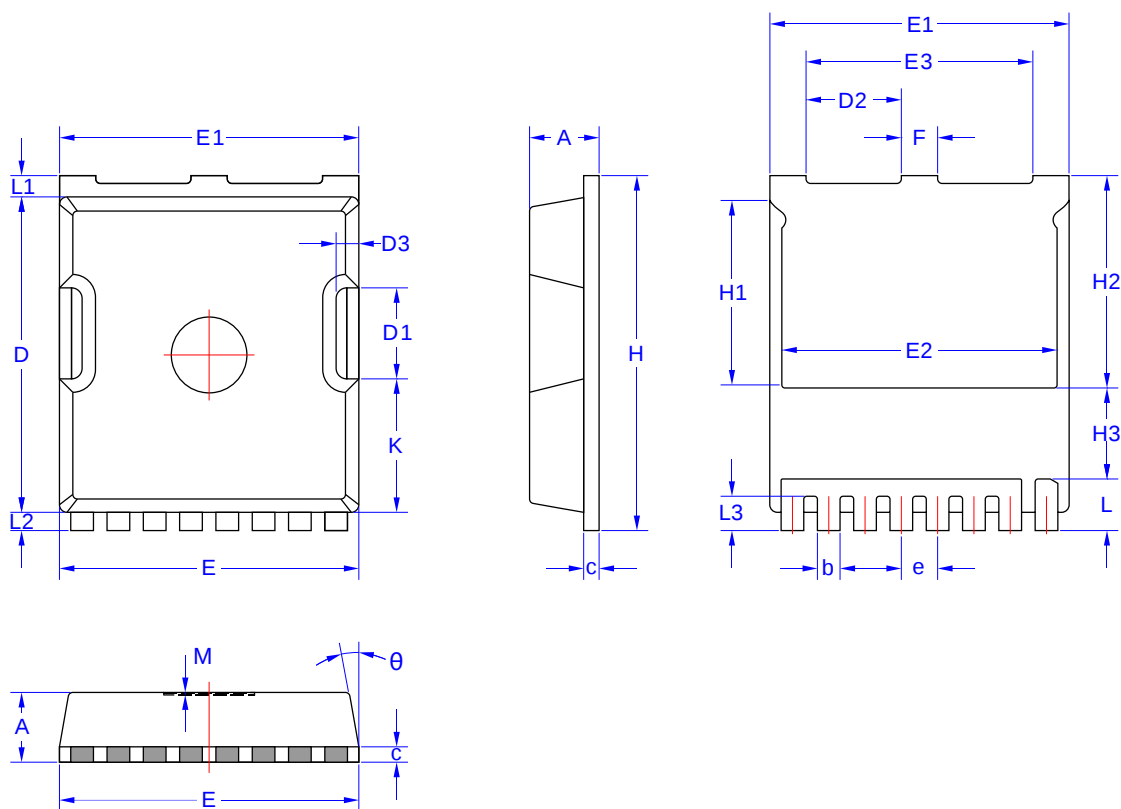


Figure 10. Maximum Continuous Drain versus Case Temperature

## 6. Package Mechanical Data

### ● TOLL-8L Package



| Symbol | Dimensions in Millimeters |           |       |
|--------|---------------------------|-----------|-------|
|        | MIN.                      | NOM.      | MAX.  |
| A      | 2.20                      | 2.30      | 2.40  |
| b      | 0.65                      | 0.75      | 0.85  |
| c      |                           | 0.508 REF |       |
| D      | 10.25                     | 10.40     | 10.55 |
| D1     | 2.85                      | 3.00      | 3.15  |
| D2     | 2.95                      | 3.10      | 3.25  |
| D3     |                           | 0.75 REF  |       |
| E      | 9.75                      | 9.90      | 10.05 |
| E1     | 9.65                      | 9.80      | 9.95  |
| E2     | 8.95                      | 9.10      | 9.25  |
| E3     | 7.25                      | 7.40      | 7.55  |
| e      |                           | 1.20 BSC  |       |

| Symbol   | Dimensions in Millimeters |          |       |
|----------|---------------------------|----------|-------|
|          | MIN.                      | NOM.     | MAX.  |
| F        | 1.05                      | 1.20     | 1.35  |
| H        | 11.55                     | 11.70    | 11.85 |
| H1       | 6.03                      | 6.18     | 6.33  |
| H2       | 6.85                      | 7.00     | 7.15  |
| H3       |                           | 3.00 BSC |       |
| K        | 4.25                      | 4.40     | 4.55  |
| L        | 1.55                      | 1.70     | 1.85  |
| L1       | 0.55                      | 0.70     | 0.85  |
| L2       | 0.45                      | 0.60     | 0.75  |
| L3       | 1.00                      | 1.15     | 1.30  |
| M        |                           | 0.08 REF |       |
| $\theta$ | 8°                        | 10°      | 12°   |